EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	83	Goldbach.inv. same Matthias	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/28 10:31
S2	1	Goldbach.inv. same Matthias and trench and substrate and "horizontal mask" and "vertical mask" and anisotropic and sidewall and etch$4 and dielectric and electrode and capacitor and insulator and connection	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 14:17
S3	1	Goldbach.inv. same Matthias and trench and substrate and "horizontal mask" and "vertical mask" and anisotropic and sidewall and etch$4 and dielectric and electrode and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 14:17
S4	1	Goldbach.inv. same Matthias and trench and substrate and "horizontal mask" and "vertical mask" and anisotropic	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 14:17
S5	37	Goldbach.inv. same Matthias and trench and substrate and mask	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 14:17
S6	23	Goldbach.inv. same Matthias and trench and substrate and mask and anisotropic	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 14:18
S7	19	Goldbach.inv. same Matthias and trench and substrate and mask and anisotropic and etch$4 and dop$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 14:18
S8	18	Goldbach.inv. same Matthias and trench and substrate and mask and anisotropic and etch$4 and dop$4 and dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 14:18
S9	8	Goldbach.inv. same Matthias and trench and substrate and mask and anisotropic and etch$4 and dop$4 and dielectric and insulator	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 14:18
S10	7	Goldbach.inv. same Matthias and trench and substrate and mask and anisotropic and etch$4 and dop$4 and dielectric and insulator and connection	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 14:27

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S11	44	"5658816"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/02 14:27
S12	930	(semiconductor or wafer or substrate) and (p-type) and (n-type) and mask and trench and (anisotropic near etch$4) and dop$4 and (dielectric or oxide) and electrode and region and insulator and connect$4 and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/28 10:35
S13	2	(semiconductor or wafer or substrate) and (p-type) and (n-type) and (vertical near mask) and trench and (anisotropic near etch$4) and dop$4 and (dielectric or oxide) and electrode and region and insulator and connect$4 and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/28 11:18
S14	46	(semiconductor or wafer or substrate) and (p-type) and (n-type) and (vertical near4 mask) and trench and (anisotropic near etch$4) and dop$4 and (dielectric or oxide) and electrode and region and insulator and connect$4 and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/28 11:23
S15	0	(semiconductor or wafer or substrate) and (p-type) and (n-type) and (vertical near4 mask) and trench and (anisotropic near etch$4) and dop$4 and (dielectric or oxide) and electrode and region and insulator and connect$4 and transistor and (438/243.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/28 11:50
S16	0	(semiconductor or wafer or substrate) and (p-type) and (n-type) and (vertical near4 mask) and trench and (anisotropic near etch$4) and dop$4 and (dielectric or oxide) and electrode and region and insulator and connect$4 and transistor and (438/243.ccls.)	USOCR	OR	ON	2006/02/28 11:50